Analog Power AM4934N

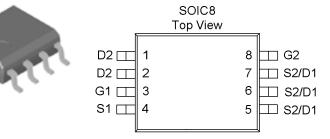
## Dual N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordlatelephones.

•	Low r <sub>DS(on)</sub> provides higher efficiency
	extends battery life

- Low thermal impedance copper leadfr SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
FET#	$r_{DS(on)}m(\Omega)$	$I_{D}(A)$			
1	$19 @ V_{GS} = 4.5V$	8.4			
1	$15 @ V_{GS} = 10V$	9.5			
2	$23 @ V_{GS} = 4.5V$	7.7			
2	$15 @ V_{GS} = 10V$	9.5			



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	FET#1	FET#1	Units	
Drain-Source Voltage	$V_{DS}$	30	30	V		
Gate-Source Voltage	$V_{GS}$	20	20	ľ		
Continue David Control	$T_A=25^{\circ}C$	$I_{\mathrm{D}}$	9.5	9.5	_	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$		7.7	7.7	Α	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	40	40			
Continuous Source Current (Diode Conduction	$I_S$	4.5	4.5	A		
D	T <sub>A</sub> =25°C	$P_{\mathrm{D}}$	2.1	2.1	W	
Power Dissipation <sup>a</sup>	$T_A=25$ °C $T_A=70$ °C		1.3	1.3		
Operating Junction and Storage Temperature	$T_J, T_{stg}$	-55 to 150		°C		

COMPLIANT HALOGEN FREE

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
M	t <= 10 sec	$ m R_{ heta JA}$	62.5	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State		110	°C/W		

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	FET#	Lim Min	its Typ	Max	Unit
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	VGS = VDS, $ID = 250  uA$	1	1			V
Gate-Tiffeshold Voltage	GS(th)	VGS = VDS, $ID = 250  uA$	2	1			•
Gate-Body Leakage	$I_{GSS}$	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	1			±100	nA
Oute Body Leakage	-055	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	2			±100	117 1
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	1			1	uA
Zero Gate Voltage Brain Current	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	2			1	uA
	ī	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	1	40			Α
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	2	40			А
	r	VGS = 10  V,  ID = 2  A	1			15	mΩ
Drain-Source On-Resistance <sup>A</sup>		VGS = 4.5  V, ID = 2  A	1			19	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	VGS = 10  V, ID = 2  A	2			15	
		VGS = 4.5  V, ID = 2  A				23	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 2A$	1		0.8		V
Drode Forward Vollage	· 3D	$I_S = -2A$	2		0.8		, The state of the
Forward Tranconductance <sup>A</sup>	g.	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$	1		64		S
Polward Tranconductance	$\mathbf{g}_{\mathrm{fs}}$	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$	2		64		S
Dynamic							
Total Gate Charge	$Q_{\mathrm{g}}$		1		3		
Total Gute Charge	₹g		2		3		пC
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =15V, $V_{GS}$ =4.5V, $I_{D}$ =2A	2		1		
		<b>1</b>	1		1		
Gate-Drain Charge	$Q_{\mathrm{gd}}$		2		1		
Turn-On Delay Time	t <sub>d(on)</sub>	N-Chaneel	2		5		
-d(on		$V_{DD}$ =15V, VGS=10V,			5 5		
Rise Time	se Time $t_{\rm r}$		2		5		_
T Off D1 T:	<b>t</b>	ID=1A , $R_{GEN}$ =25 $\Omega$ , P-Channel	1		16		nS
Turn-Off Delay Time	$t_{d(off)}$	VDD=-15V, VGS=-10V,	2		16		
Fall-Time	$t_{\mathrm{f}}$	ID=-1A RGEN=15 $\Omega$	2		7		
Notes			7		/		

## Notes

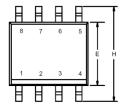
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

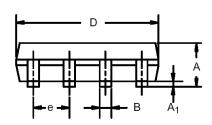
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## Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

